

Title (en)  
METHOD FOR SURFACTANT CRYSTAL GROWTH OF A METAL-NONMETAL COMPOUND

Title (de)  
VERFAHREN ZUR TENSIDKRISTALLZÜCHTUNG EINER METALL-NICHTMETALL-VERBINDUNG

Title (fr)  
PROCÉDÉ DE CROISSANCE CRISTALLINE EN PRÉSENCE D'UN TENSIOACTIF À BASE D'UN COMPOSÉ MÉTALLIQUE/NON-MÉTALLIQUE

Publication  
**EP 2688847 A1 20140129 (EN)**

Application  
**EP 12715208 A 20120304**

Priority

- US 201161449421 P 20110304
- IL 2012000103 W 20120304

Abstract (en)  
[origin: WO2012120497A1] Method for crystal growth from a surfactant of a metal-nonmetal (MN) compound, including the procedures of providing a seed crystal, introducing atoms of a first metal to contact with the seed crystal thus forming a thin liquid metal wetting layer on a surface of the seed crystal, setting a temperature of the seed crystal below a minimal temperature required for dissolving MN molecules in the wetting layer and above a melting point of the first metal, each one of the MN molecules being formed from an atom of a second metal and an atom of a first nonmetal, introducing the MN molecules which form an MN surfactant monolayer, thereby facilitating a formation of the wetting layer between the MN surfactant monolayer and the surface of the seed crystal, and regulating a thickness of the wetting layer, thereby growing an epitaxial layer of the MN compound on the seed crystal.

IPC 8 full level  
**C30B 9/00** (2006.01); **C30B 7/00** (2006.01); **C30B 19/00** (2006.01); **C30B 19/06** (2006.01); **C30B 19/10** (2006.01); **C30B 23/00** (2006.01); **C30B 23/02** (2006.01); **C30B 25/00** (2006.01); **C30B 25/02** (2006.01); **C30B 25/16** (2006.01); **C30B 29/40** (2006.01)

CPC (source: EP KR US)  
**C30B 7/005** (2013.01 - US); **C30B 9/00** (2013.01 - EP US); **C30B 15/04** (2013.01 - KR); **C30B 19/00** (2013.01 - US); **C30B 19/02** (2013.01 - KR); **C30B 19/068** (2013.01 - EP US); **C30B 19/10** (2013.01 - EP US); **C30B 23/00** (2013.01 - EP US); **C30B 23/002** (2013.01 - EP US); **C30B 23/02** (2013.01 - US); **C30B 25/00** (2013.01 - EP US); **C30B 25/02** (2013.01 - US); **C30B 25/16** (2013.01 - EP US); **C30B 29/40** (2013.01 - EP US)

Citation (search report)  
See references of WO 2012120497A1

Designated contracting state (EPC)  
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

DOCDB simple family (publication)  
**WO 2012120497 A1 20120913**; **WO 2012120497 A4 20121101**; AU 2012226395 A1 20131003; BR 112013022384 A2 20161206; CA 2829064 A1 20120913; CN 103562149 A 20140205; EP 2688847 A1 20140129; JP 2014508415 A 20140403; KR 20140024303 A 20140228; US 2013333613 A1 20131219; US 8945302 B2 20150203

DOCDB simple family (application)  
**IL 2012000103 W 20120304**; AU 2012226395 A 20120304; BR 112013022384 A 20120304; CA 2829064 A 20120304; CN 201280019383 A 20120304; EP 12715208 A 20120304; JP 2013555991 A 20120304; KR 20137026180 A 20120304; US 201214002820 A 20120304